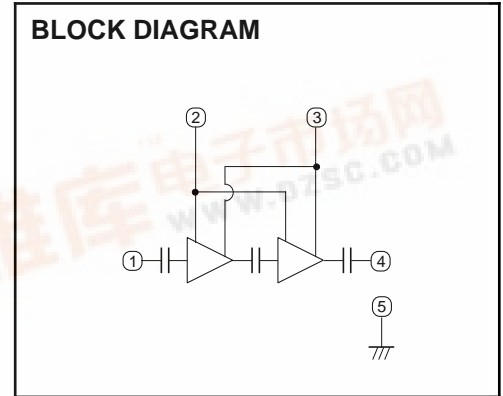
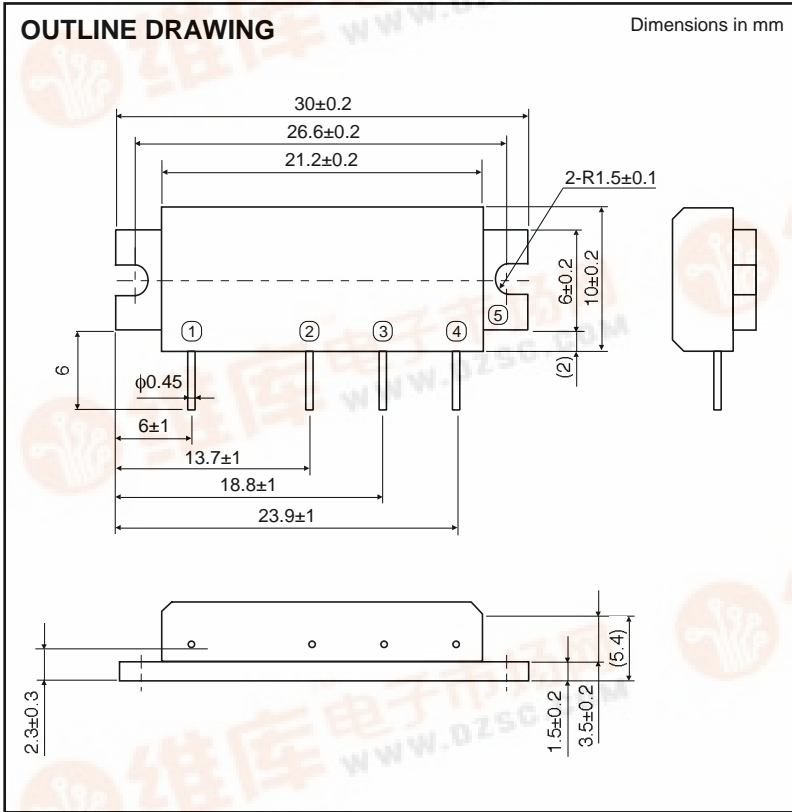


MITSUBISHI RF POWER MODULE

M68732L

SILICON MOS FET POWER AMPLIFIER, 400-430MHz, 7W, FM PORTABLE RADIO



PIN:

- ①Pin : RF INPUT
- ②VGG : GATE BIAS SUPPLY
- ③VDD : DRAIN BIAS SUPPLY
- ④Po : RF OUTPUT
- ⑤GND: FIN

ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

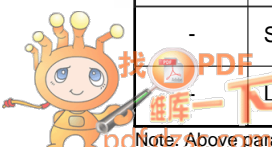
Symbol	Parameter	Conditions	Ratings	Unit
VDD	Supply voltage	VGG 3.5V, ZG=ZL=50	9.2	V
VGG	Gate bias voltage		4	V
Pin	Input power	f=400-430MHz, ZG=ZL=50	70	mW
Po	Output power	f=400-430MHz, ZG=ZL=50	10	W
Tc (OP)	Operation case temperature	f=400-430MHz, ZG=ZL=50	-30 to +100	°C
Tstg	Storage temperature		-40 to +110	°C

Note. Above parameters are guaranteed independently.

ELECTRICAL CHARACTERISTICS (Tc=25°C, ZG=ZL=50 unless otherwise noted)

Symbol	Parameter	Test conditions	Limits		Unit	
			Min	Max		
f	Frequency range		400	430	MHz	
Po	Output power	VDD=7.2V, VGG=3.5V, Pin=50mW	7		W	
η	Total efficiency		45		%	
2fo	2nd. harmonic			-25		dBc
in	Input VSWR			4		-
-	Stability	ZG=50, VDD=4-19.2V, Load VSWR<4:1	No parasitic oscillation		-	
-	Load VSWR tolerance	VDD=9.2V, Pin=50mW, Po=7W (VGG adjust), ZL=20:1	No degradation or destroy		-	

Note. Above parameters, ratings, limits and test conditions are subject to change.



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TYPICAL PERFORMANCE DATA

